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SPACER AND PROCESS TO ENHANCE THE STRAIN IN THE CHANNEL WITH STRESS LINER

ABSTRACT

Process for enhancing strain in a channel with a stress liner, spacer, process for forming integrated circuit and integrated circuit. A first spacer (50) composed of a first oxide (130) and first nitride (40) layer is applied to a gate electrode (10) on a substrate (20), and a second spacer (60) composed of a second oxide (70) and a second nitride (80) layer is applied. Deep implanting of source and drain in the substrate (20) occurs, and removal of the second nitride (80), second oxide (70), and first nitride layers (40).



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Fig. 9.